

**Amendments to the Claims:**

1 - 25 Canceled

26. (Original) A method for fabricating a highly transparent and highly efficient organic light emitting device comprising:

preparing, in sequence on a substrate, an anode, an organic hole transporting layer, an organic electron transporting layer, a transparent electron injection layer, and a transparent electron injecting layer, wherein said transparent electron injection layer is a material selected from the group consisting of a material which acts as a hole blocking layer, a material which acts as an exciton blocking material and a material which acts as a combination hole and exciton blocking material; and

wherein said preparing includes the step of doping said transparent electron injection layer with a metal to form a metal-doped transparent electron injection layer.

27. (Original) The method according to claim 26 wherein said transparent electron injection layer is doped with said metal by depositing an ultra-thin layer of said metal on said organic electron transporting layer prior to depositing said transparent electron injection layer.

28. (Original) The method according to claim 26 wherein said transparent electron injection layer is doped with said metal by depositing an ultra-thin layer of said metal on said transparent electron injection layer prior to depositing said transparent electron injecting layer.

29. (Original) The method according to claim 26 wherein said transparent electron injecting layer comprises ITO.

30. (Original) The method according to claim 27 wherein said ultra-thin layer of said metal has a thickness of 5-10 Å.

31. (Original) The method according to claim 27, wherein said metal comprises a metal selected from the group consisting of Li, Sr and Sm.

32. (Original) The method according to claim 27, wherein said metal comprises Li.

33. (Original) The method according to claim 26, wherein said metal-doped transparent electron injection layer comprises 2,9-dimethyl-4,7-diphenyl-1,10-phenanthroline.
34. (Original) The method according to claim 26, wherein said metal-doped transparent electron injection layer has a metal atom density sufficient to produce an electronic density of at least about  $10^{15}/\text{cm}^3$ .
35. (Original) The method according to claim 26, wherein said metal-doped transparent electron injection layer has a metal atom density sufficient to produce an electronic density of at least about  $10^{21}/\text{cm}^3$ .
36. (Original) The method according to claim 26, wherein said metal-doped transparent electron injection layer has a metal atom density sufficient to produce a total external quantum efficiency of at least 1 % for said organic light emitting device.
37. (Original) The method according to claim 26, wherein said hole transporting layer comprises 4,4-bis[N-(1-naphthyl)-N-phenyl-amino] biphenyl.
38. (Original) The method according to claim 26, wherein said electron transporting layer comprises tris-(8-hydroxyquinoline) aluminum.

39-45 Canceled